

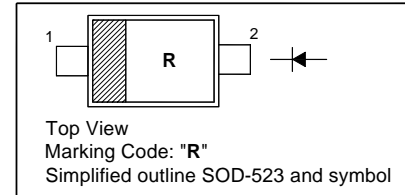
1SS420

Silicon Epitaxial Planar Schottky Barrier Diode

for high speed switching application

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |

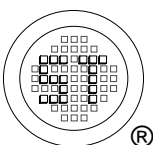


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|-----------------------------|-------------|---------------|------------------|
| Peak Reverse Voltage | V_{RM} | 35 | V |
| Reverse Voltage | V_R | 30 | V |
| Average Forward Current | $I_{F(AV)}$ | 200 | mA |
| Peak Forward Current | I_{FM} | 300 | mA |
| Power Dissipation | P_{tot} | 150 | mW |
| Surge Current (10 ms) | I_{FSM} | 1 | A |
| Junction Temperature | T_j | 125 | $^\circ\text{C}$ |
| Operating Temperature Range | T_{opr} | - 40 to + 100 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | - 55 to + 125 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

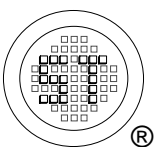
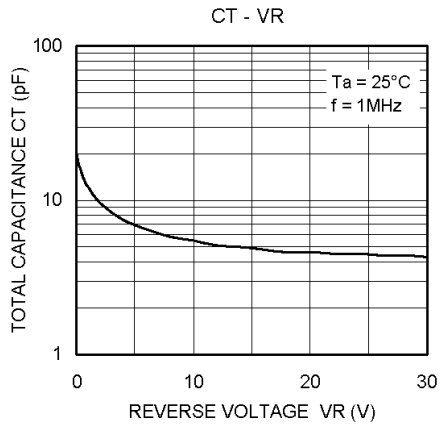
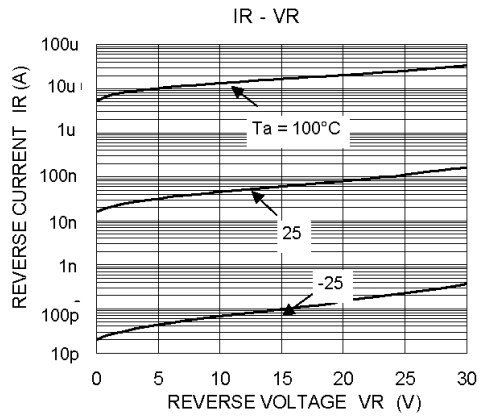
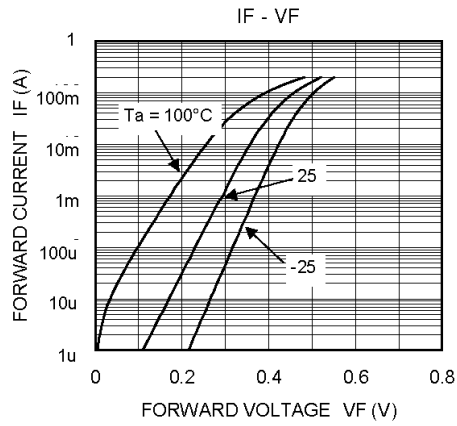
| Parameter | Symbol | Typ. | Max. | Unit |
|---|--------|------|------|---------------|
| Forward Voltage at $I_F = 200\text{ mA}$ | V_F | - | 0.6 | V |
| Reverse Current at $V_R = 30\text{ V}$ | I_R | - | 5 | μA |
| Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$ | C_T | 20 | - | pF |



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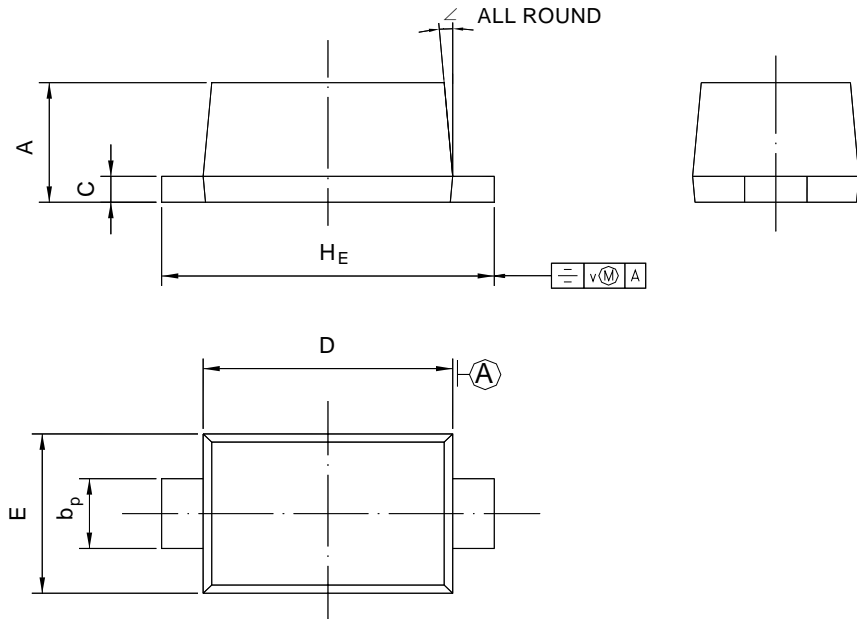


1SS420

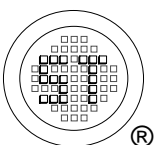
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



| UNIT | A | b _p | C | D | E | H _E | V | ∠ |
|------|--------------|----------------|----------------|--------------|--------------|----------------|-----|----|
| mm | 0.70 0.60 | 0.4 0.3 | 0.135 0.100 | 1.25 1.15 | 0.85 0.75 | 1.7 1.5 | 0.1 | 5° |



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